

Amendments to the Specification

Please replace paragraph [0002] with the following rewritten paragraph:

[0002] Conventionally, an electrostatic capacitance detection device used for fingerprint sensor or the like is formed of a sensor electrode and a dielectric layer, provided on the sensor electrode, on a single crystal ~~silicon~~silicon substrate. See, for example, Japanese laid-open patent publication No. 11-118415, No. 12-346608, No. 13-56204 and No. 13-133213). FIG. 1 shows an operating principle of the conventional electrostatic capacitance detection device. A sensor electrode and a dielectric layer form an electrode and a dielectric layer of a capacitor, and a human body becomes the other electrode, which is grounded. The electrostatic capacitance  $C_F$  of this capacitor changes depending on the indentation of a fingerprint contacting the surface of the dielectric layer. A capacitor having the electrostatic capacitance  $C_S$  is prepared on the semiconductor substrate, and the two capacitors are coupled in series and a predetermined voltage is applied thereon. This allows an electric charge  $Q$  to be generated between the two capacitors depending on the indentation of the fingerprint. The electric charge  $Q$  can be detected using a usual semiconductor technology, and surface contours of the object can be read.

Please replace paragraph [0003] with the following rewritten paragraph:

[0003] However, because the conventional electrostatic capacitance detection devices are formed on a single crystal ~~silicon~~silicon substrate, there has been a problem that the devices are cracked when a finger is strongly pressed thereon when used for a fingerprint sensor. Furthermore, the fingerprint sensor inevitably requires a size of approximately 20 mm x 20 mm for its application, and most of the area of the electrostatic capacitance detection device is dominated by a sensor electrode. The sensor electrode is, of course, formed on the single crystal ~~silicon~~silicon substrate, however, most area of the single crystal ~~silicon~~silicon substrate (beneath the sensor electrode), which is produced by consuming large amount of resources and labor, only plays a role of a supporting body. In other words, there has been a problem that the conventional electrostatic capacitance detection devices are not only expensive, but also have a large amount of waste and expense associated with their manufacture.

Please replace paragraph [0004] with the following rewritten paragraph:

[0004] In addition, it is recently required strongly that a personal authenticating function is provided on cards, such as credit card and cash card, to enhance safety of cards. However, there has been a problem that the electrostatic capacitance detection devices manufactured on the conventional single crystal ~~silicon~~silicon substrate is not so flexible, therefore, the devices cannot be manufactured on a plastic substrate.